

RAD7230-NNJx Power MOSFET in SMD 0.5 Package

Datasheet

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www.aeroflex.com/MOSFETS



FEATURES

- ❑ 200V breakdown voltage
- ❑ 12 A current rating
- ❑ $0.22\Omega R_{DS(on)}$
- ❑ 160nC gate charge
- ❑ -55°C to $+125^{\circ}\text{C}$ temperature range
- ❑ Operational Environment radiation testing to MIL-STD-750
 - Total-dose: 100 krad(Si)
 - SEGR/SEB immune to Xe at full rated drain potential
- ❑ Bare die also available
 - Prototypes, EMs and Class S
- ❑ Drop-in compatible with industry standards
- ❑ Class S MOSFETs built to your custom flow

INTRODUCTION

Aeroflex RAD's new radiation tolerant power MOSFETs are now available in die, seven standard package options and custom packaging for HiRel environments. Applications within military, aerospace, medical, nuclear power generation, high energy physics research laboratories can benefit from the use of this new series of MOSFETs. Aeroflex's Power MOSFETs are radiation tolerant to 100 krad(Si) and SEGR/SEB immune to their full rated breakdown potential.

Operational power losses are minimized by Aeroflex's ideal combination of low $R_{DS(on)}$ and gate charge. Die size is optimized for maximum current rating while meeting industry norms. These units are suitable for standalone and hybrid applications.

The RAD7230-NNJx packaged in the popular SMD 0.5 are well suited for low loss switching applications, such as DC-to-DC Converters and solid-state relays. They are drop-in compatible with industry standards.

ELECTRICAL CHARACTERISTICS (Case temperature (T_c) = 25°C unless otherwise specified)

CHARACTERISTICS		TEST CONDITIONS		LIMITS			UNITS
				MIN	TYP	MAX	
Drain-Source Breakdown Voltage	BV_{dss}	$V_{gs} = 0V, I_d = 1mA$		200	-	-	V
Gate-Threshold Voltage	$V_{gs(th)}$	$V_{ds} = V_{gs}, I_d = 1.0mA$		2.0	-	4.0	V
Gate-Body Leakage	I_{gss}	$V_{gs} = \pm 20V$		-	-	100	nA
Zero-Gate Leakage	I_{dss1}	$V_{ds} = 160V, V_{gs} = 0V$		-	-	25	μA
Drain Current	I_{dss2}	$V_{ds} = 1600V, V_{gs} = 0V, T_c = 125^{\circ}\text{C}$		-	-	250	
Drain-Source On Resistance	$R_{DS(on)}$	$V_{gs} = 12V, I_d = 9.6A$		-	-	0.22	ohms
Gate to Source Charge	Q_{gs}	$V_{gs} = 0V$ to $12V$	$I_d = 12A$ $V_{dd} = 125V$	-	-	10	nC
Diode Forward Voltage	V_{sd}	$I_d = 12A, V_{gd} = 0V$		0.6	-	1.8	V
Continuous source current (body diode)	I_s			-	-	13	A

POST-RADIATION ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	TEST CONDITIONS	LIMITS		UNITS	
		MIN	MAX		
Drain-Source Breakdown Voltage ^{3,4}	Bvdss	Vgs = 0V, Id = 1mA	200	-	V
Gate-Source Threshold Voltage ^{3,4}	Vgs(th)	Vgs = Vds, Id = 1.0mA	1.5	4.0	V
Gate-Body Leakage Forward ^{2,3,4}	Igss	Vgs = ±20, Vds = 0V	-	100	nA
Zero-Gate Voltage Drain Current ^{3,4}	Idss	Vgs = 0V, Vds = 160V	-	25	μA
Drain-Source On-Resistance ^{1,3,4}	R _{DS(on)}	Vgs = 12V, Ids = 9.6A	-	0.22	ohms

Notes:* for die products, the maximum current may be limited by packaging

1. Pulse test, 300us max
2. Absolute value
3. Gamma = 100 krad(Si)
4. Gamma irradiation bias at both Vgs = 12V, Vds = 0V and Vgs = 0V, Vds = 80% BVdss

SEE (SINGLE-EVENT-EFFECTS)

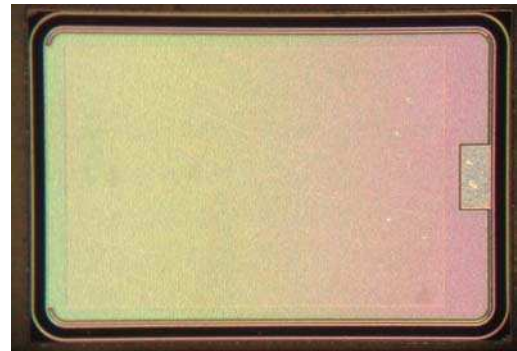
CHARACTERISTICS	SYMBOL	ENVIRONMENT ¹				MAX VDS BIAS (V) ²
		ENERGY (MeV)	TYPICAL LET (MEV/MG/CM2)	TYPICAL RANGE (u)	APPLIED VGS BIAS (V)	
Single Event Effects - Safe Operating Area	Kr	906	30	113	-10	200
	Xe	1232	59	99	-5	200

Notes:

1. Fluence = 1E6 ions/cm² (typical), T = 25°C
2. Does not exhibit Single Event Burnout (SEB) or Single Event Gate Rupture (SEGR).

DIE FEATURES

- Die Size
 - 126mils ± 2mils x 182mils ± 2mils
- Gate Pad
 - .011" ± 1mil x 0.25 ± 1.5mils
- Die Thickness
 - 14 mils ± 1mils
- Top Metal
 - 40kA (±10%) Al 1% Si
- Back Metal
 - Ti(2kA)NiV(10kA)Ag(2kA) (±10%)



ELECTRICAL TESTING AT WAFER PROBE:

ITEM	VOLTAGE	CURRENT	LOWER LIMIT	UPPER LIMIT	LOWER SPEC	UPPER SPEC	UNIT
igss	Vgs=5V			100			uA
igss	Vgs=20V			100		100	nA
igss	Vgs=30V			1			uA
idss	Vds=120V			2		25	uA
idss	Vds=150V			10		1000	uA
bvdss		Ids=1mA	200		200		V
R _{DS(on)}	Vgs=12V	Ids=0.5A		220		220	mΩ
R _{DS(on)}	Vgs=12V	Ids=2A		220		220	mΩ
vsd		Isd=2A	0.6	1.2	0.6	1.8	V
vth		Ids=250μA	2.7	3.9	2.00	4.00	V
igssr	Vgs=-20V			100		100	nA
igssr	Vgs=-30V			1			uA
idss	Vds=150V			10			uA
igss	Vgs=20V			100		100	nA

AEROFLEX RAD RAD7230-NNJx PART NUMBERING:

PART #	BREAKDOWN POTENTIAL (V)	R _{DS(on)} (mΩ)	DRAIN CURRENT (A)	GATE CHARGE (nC)	TID LEVEL (krad(SI))	SEE	Die size	PKG	SCREENING
RAD7230-NNJP	200	220	12	10	100	Xe	3	SMD 0.5	Prototype
RAD7230-NNJE	200	220	12	10	100	Xe	3	SMD 0.5	EM
RAD7230-NNJS	200	220	12	10	100	Xe	3	SMD 0.5	Space

Aeroflex RAD- Datasheet Definition

Advanced Datasheet - Product In Development

Preliminary Datasheet - Shipping Prototypes

Datasheet - Class S Compliant, QML or JAN

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